

Angle-resolved photoemission study of $\text{Bi}_2\text{Sr}_{1.6}\text{Ln}_{0.4}\text{CuO}_6$ ($\text{Ln}=\text{La}, \text{Gd}$) with controlled out-of-plane disorder

Makoto HASHIMOTO^{1*}, Tepei YOSHIDA¹, Masaki IKEDA¹, Satoru KUDO¹,
Atsushi FUJIMORI¹, Nozomu KAMAKURA², Masato KUBOTA², Kanta ONO², Kazuhiro FUJITA¹,
Shinichi UCHIDA¹

¹Department of Physics, The University of Tokyo, Bunkyo-ku, Tokyo 113-0033, Japan

²KEK-PF, Tsukuba, Ibaraki 305-0801, Japan

In high- T_c cuprates, the effects of impurity or disorder have been widely discussed. The effects of Zn or Ni substitution in the CuO_2 plane have been studied by angle-resolved photoemission spectroscopy (ARPES) and the electronic structural change caused by the impurities has been revealed [1, 2]. Recently, in addition to the in-plane disorder, the importance of out-of-plane disorder has been pointed out [3, 4]. The out-of-plane disorder reduces T_c as in the case of in-plane disorder. We have performed ARPES study of $\text{Bi}_2\text{Sr}_{1.6}\text{Ln}_{0.4}\text{CuO}_{6+\delta}$ (Ln -Bi2201, $\text{Ln} = \text{La}, \text{Gd}$) with controlled out-of-plane disorder, where Gd-Bi2201 is much disordered than La-Bi2201, to reveal the effects of the disorder on the electronic structure.

The measured samples were optimally doped La-Bi2201 ($T_c = 34$ K) and Gd-Bi2201 ($T_c = 13$ K), which were prepared by the traveling solvent floating zone (TSFZ) method [3]. The ARPES measurements were performed at BL28A equipped with a SCIENTA SES2002 analyzer and a 5-axis i -gonio manipulator [5]. The photon energy was 50 eV. The total energy and angular resolution were set at ~ 15 meV and 0.3 degree, respectively. The measurement temperature was ~ 9 K. The samples were cleaved *in-situ* to obtain clean surfaces.

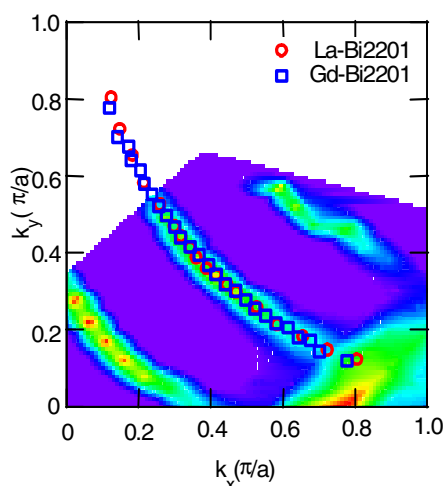


Fig. 1: k -space intensity plot of La-Bi2201. The open red circles and open blue squares show the Fermi surfaces of La-Bi2201 and Gd-Bi2201 determined from the MDC peak positions.

Figure 1 shows the k -space intensity plot for 20 meV around E_F for La-Bi2201. The circles and the squares in the figure show the Fermi surfaces determined from the MDC (momentum distribution curve) for La- and Gd-Bi2201, respectively. The shapes of the Fermi surface did not change with disorder, which means the hole concentration is exactly the same and suggest that the next-nearest-hopping integral t' did not change with disorder.

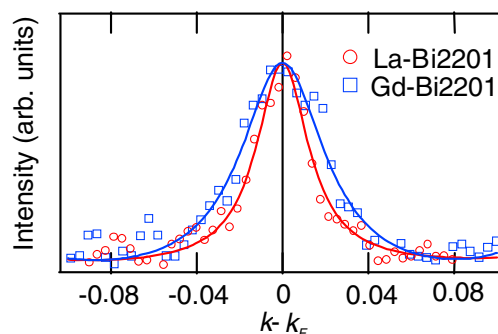


Fig. 2: MDC width along the nodal direction. The open circles are for La-Bi2201 and the open squares are for Gd-Bi2201.

Figure 2 shows the MDC at E_F along the nodal $(0, 0)-(\pi, \pi)$ direction for La- and Gd-Bi2201. One can see the width of the MDC (Δ_k) becomes larger with increasing disorder, which is due to the increase of the scattering of carriers by the disorder and is consistent with the results of the in-plane residual resistivity. The results suggest that the scattering in the nodal direction plays an important role in the depression of T_c .

References

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* hashimot@wyvern.phys.s.u-tokyo.ac.jp